

Notice of References Cited	Application/Control No. 10/540,513	Applicant(s)/Patent Under Reexamination OSADA ET AL.	
	Examiner Eduardo A. Rodela	Art Unit 2826	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,831,296	11-1998	Kuroda et al.	257/194
	B	US-			
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	K	US-			
	L	US-			
	M	US-			

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NON-PATENT DOCUMENTS

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.